

Fast switching diode chip in Emitter Controlled -Technology

Features:

- 1700V technology, Emitter Controlled
- soft, fast switching
- low reverse recovery charge
- small temperature coefficient

This chip is used for:

• power modules and discrete devices



Applications:

• SMPS, resonant applications, drives

| Chip Type | V _R | I _F | Die Size | Package |
|---------------|----------------|----------------|-----------------------------|--------------|
| SIDC73 D170E6 | 1700V | 100A | 8.53 x 8.53 mm ² | sawn on foil |

Mechanical Parameter

| Mechanical Parameter | | | |
|---------------------------------|---|-----------------|--|
| Raster size | 8.53 x 8.53 | | |
| Area total | 72.76 | mm ² | |
| Anode pad size | 6.51 x 6.51 | | |
| Thickness | 200 | μm | |
| Wafer size | 150 | mm | |
| Max. possible chips per wafer | 189 | | |
| Passivation frontside | Photoimide | | |
| Pad metal | 3200 nm AlSiCu | | |
| Backside metal | Ni Ag-system suitable for epoxy and soft solder die bonding | | |
| Die bond | Electrically conductive glue or solder | | |
| Wire bond | Al, ≤500µm | | |
| Reject ink dot size | Ø 0.65mm; max 1.2mm | | |
| Recommended storage environment | Store in original container, in dry nitrogen, in dark environment, < 6 month at an ambient temperature of 23°C | | |



Maximum Ratings

| Parameter | Symbol | Condition | Value | Unit | |
|------------------------------------|------------------|--|---------|------|--|
| Repetitive peak reverse voltage | V _{RRM} | <i>T</i> _{vj} = 25 °C | 1700 | V | |
| Continuous forward current | I _F | <i>T</i> _{vj} < 150°C | 1) | A | |
| Maximum repetitive forward current | I _{FRM} | <i>T</i> _{vj} < 150°C | 200 | | |
| Junction temperature range | T _{vj} | | -40+175 | °C | |
| Operating junction temperature | T _{vj} | | -40+150 | °C | |
| Dynamic ruggedness ²⁾ | P _{max} | $I_{\rm Fmax}$ = 200A, $V_{\rm Rmax}$ = 1700V $T_{\rm vj} \le 150^{\circ}{\rm C}$ | tbd | kW | |

¹⁾ depending on thermal properties of assembly

²⁾ not subject to production test - verified by design/characterisation

Static Characteristic (tested on wafer), $T_{vj} = 25 \text{ °C}$

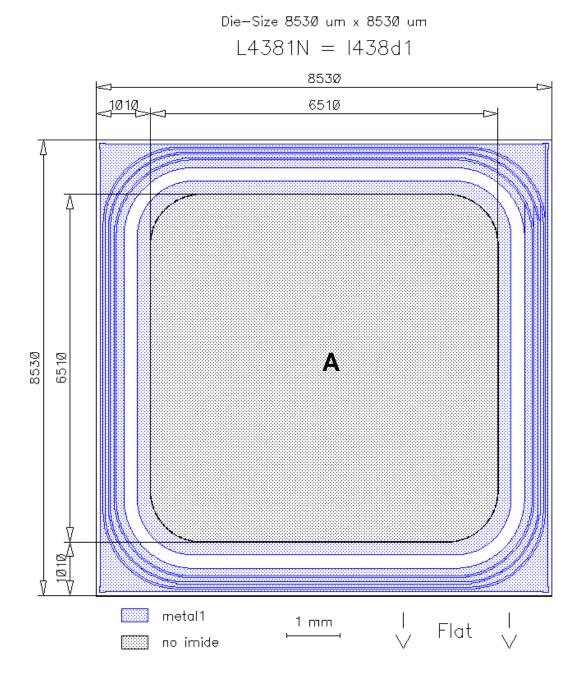
| Parameter | Symbol | Conditions | Value | | | Unit |
|-----------------------------------|-----------------|-----------------------|-------|------|------|------|
| | | | min. | typ. | max. | Onne |
| Reverse leakage current | I _R | V _R =1700V | | | 27 | μA |
| Cathode - Anode breakdown Voltage | V _{BR} | / _R =4m A | 1700 | | | V |
| Diode forward voltage | V _F | / _F =100A | | 2.15 | | V |

Further Electrical Characteristic

Switching characteristics and thermal properties are depending strongly on module design and mounting technology and can therefore not be specified for a bare die.



Chip Drawing



A: Anode pad

Edited by INFINEON Technologies, AIM PMD D CID CLS, L4381N, Edition 1.2, 28.07.2008



Description

AQL 0.65 for visual inspection according to failure catalogue

Electrostatic Discharge Sensitive Device according to MIL-STD 883

Published by Infineon Technologies AG 81726 Munich, Germany © 2008 Infineon Technologies AG All Rights Reserved.

Legal Disclaimer

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics. With respect to any examples or hints given herein, any typical values stated herein and/or any information regarding the application of the device, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation, warranties of non-infringement of intellectual property rights of any third party.

Information

For further information on technology, delivery terms and conditions and prices, please contact the nearest Infineon Technologies Office (www.infineon.com).

Warnings

Due to technical requirements, components may contain dangerous substances. For information on the types in question, please contact the nearest Infineon Technologies Office. Infineon Technologies components may be used in life-support devices or systems only with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support device or system or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.